

RADIATION
EFFECTS
IN
ELECTRONICS



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RADIATION EFFECTS IN ELECTRONICS

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F O R E W O R D

The contents of this volume resulted from a joint effort of ASTM Committee E-10 on Radioisotopes and Radiation Effects and the Niagara-Finger Lakes Section of the American Nuclear Soc., and consists of the major portion of the transactions of the Joint ANS-ASTM Conference on Radiation Effects in Electronics. This meeting convened at the Hotel Syracuse, Syracuse, N. Y., Oct. 5 to 7, 1964. Approximately 170 engineers and scientists registered for the meeting.

This volume is commended to those scientists and engineers engaged in work with basic solid state electronic devices in applications where nuclear or space radiation is part of the environment. Others engaged in work in nuclear or astronautical fields undoubtedly should be interested in these proceedings. Committee E-10 takes pleasure in presenting this volume as a record of this significant and timely meeting.

NOTE—The Society is not responsible, as a body, for the statements
and opinions advanced in this publication

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